

FIG. 1

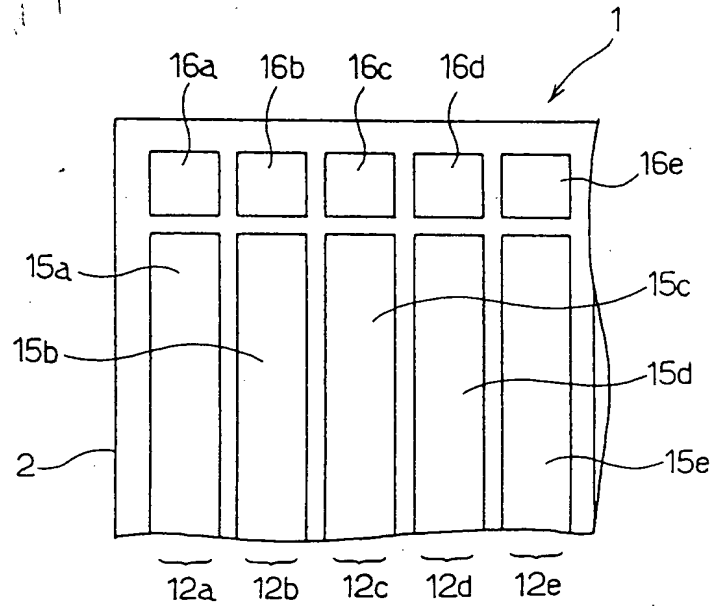


FIG. 2

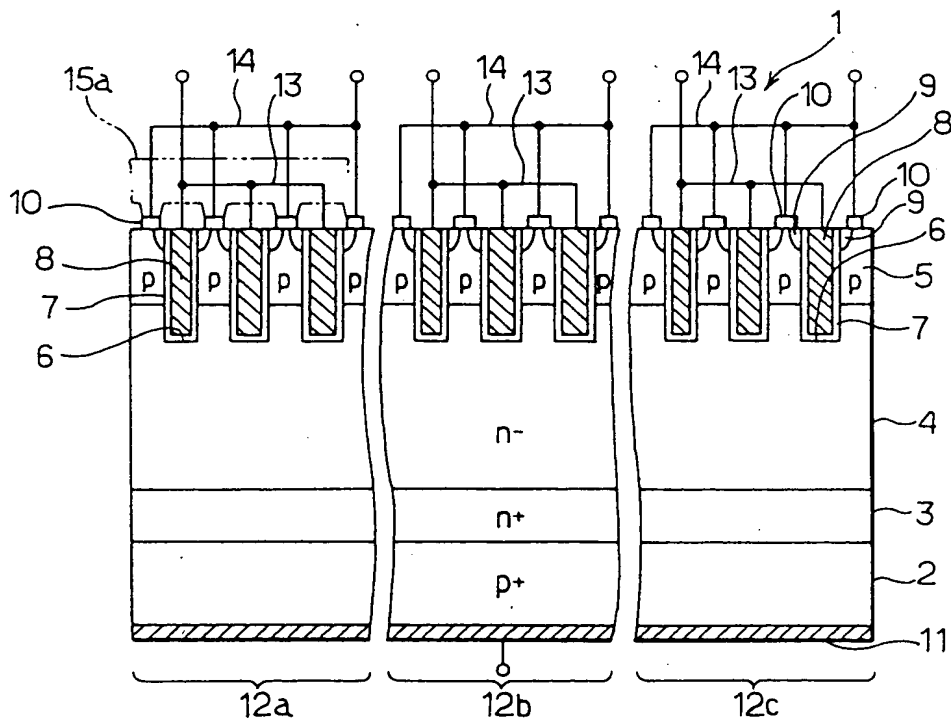


FIG. 3

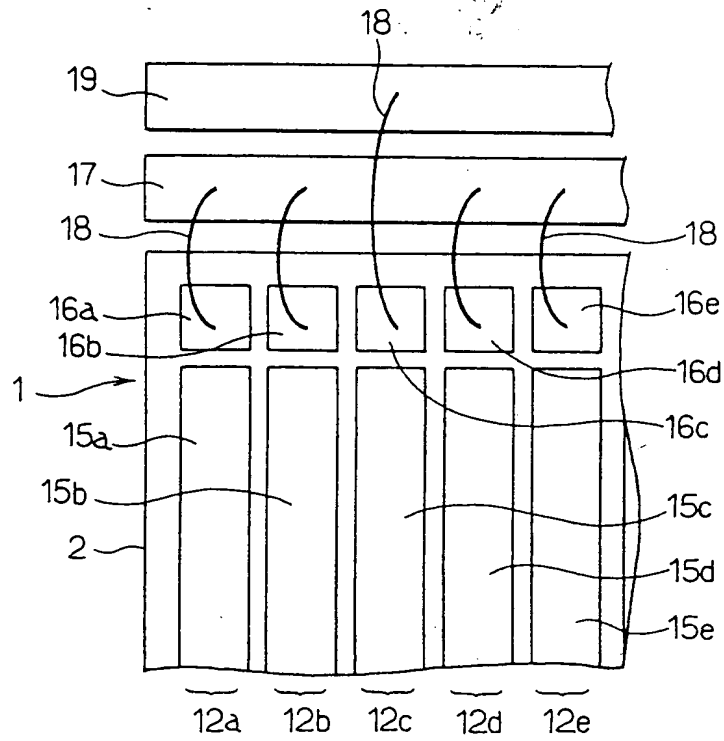
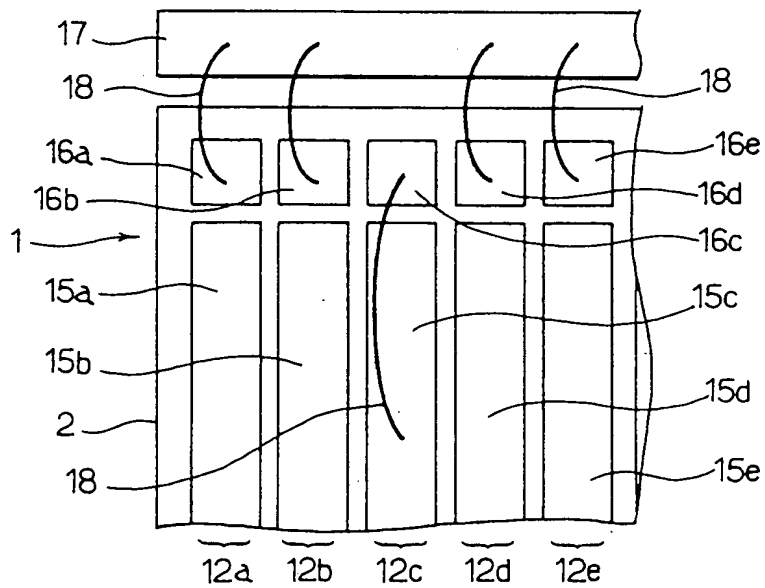
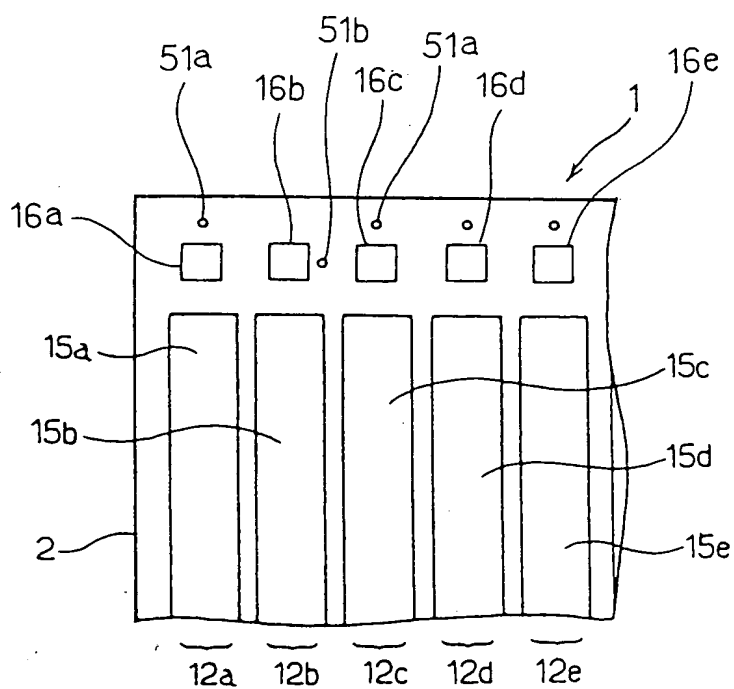


FIG. 4



A cross-sectional view of a semiconductor device assembly. A substrate 20 is shown at the bottom. On top of the substrate, there is a layer 22. Above layer 22, there is a stack of layers: a bottom layer 23, a middle layer 21, and a top layer 16. A layer 15 is positioned above the stack of layers 23, 21, and 16. A layer 2 is positioned above layer 15. A layer 1 is positioned above layer 2. The layers 23, 21, and 16 are shown with different hatching patterns: diagonal lines for 23, dots for 21, and horizontal lines for 16.



[illegible]

FIG. 9

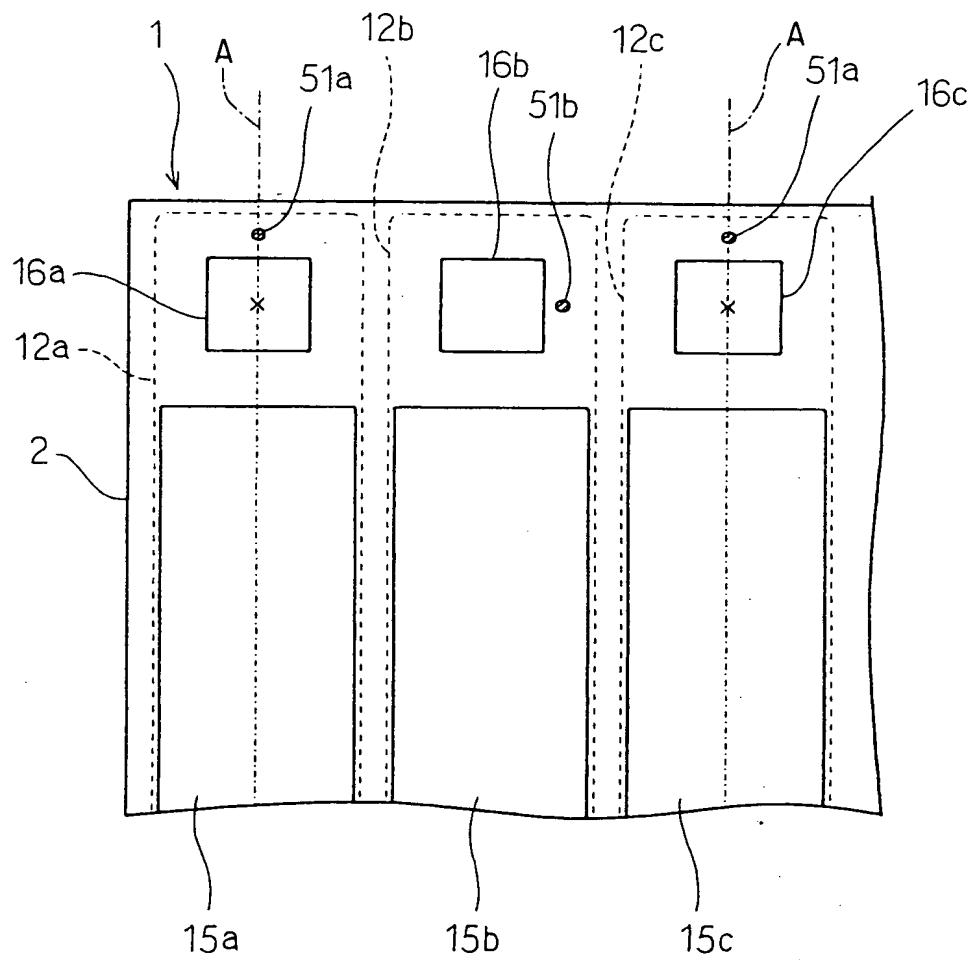


FIG. 10

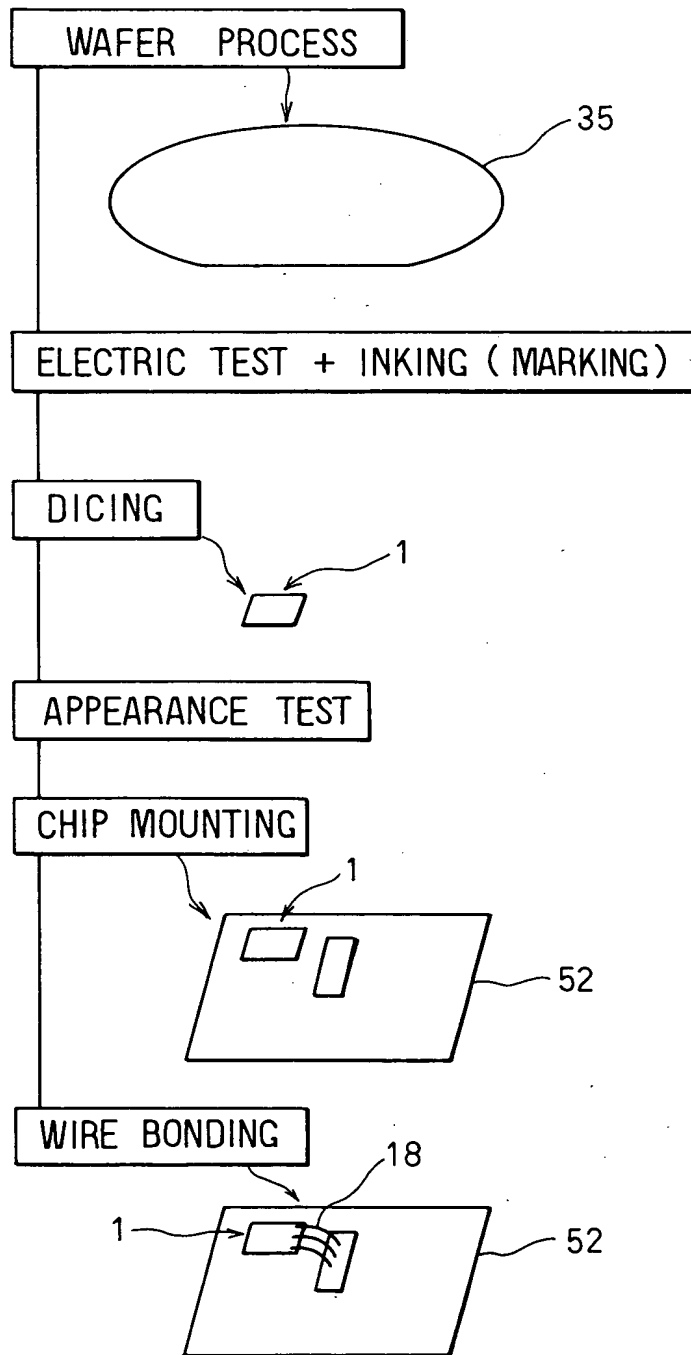


FIG. 11

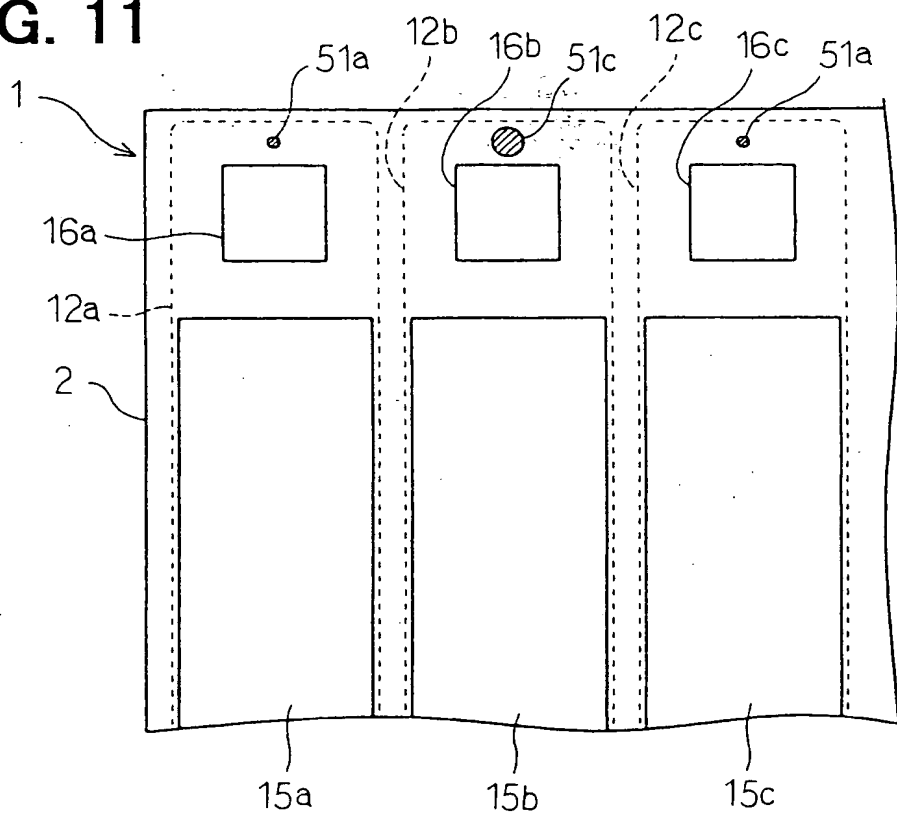


FIG. 12

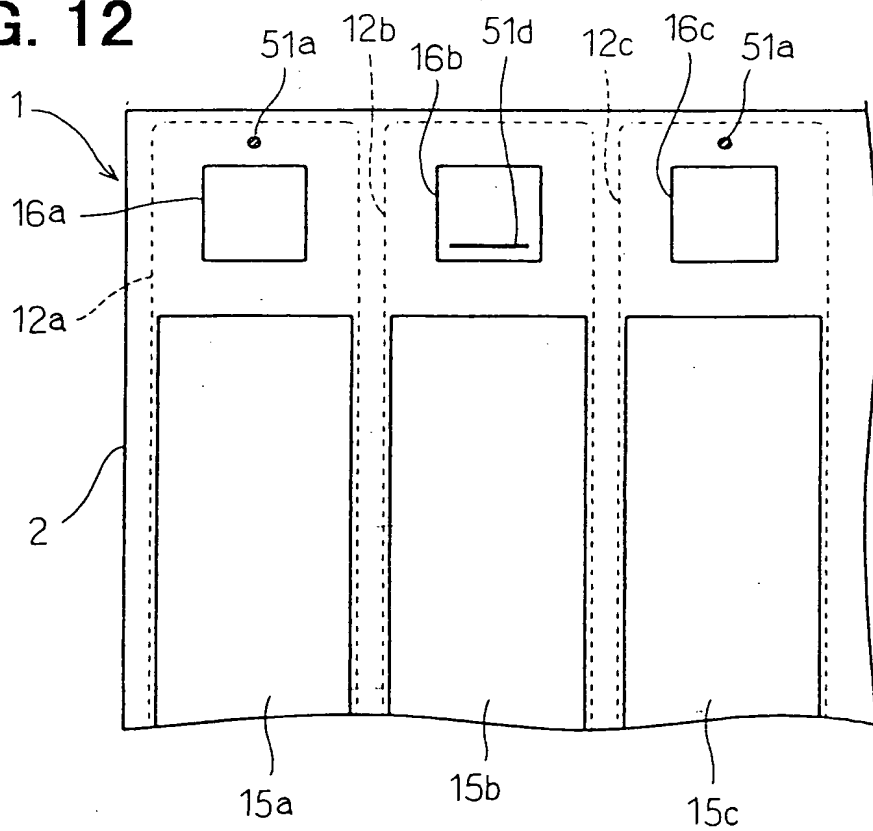


FIG. 13

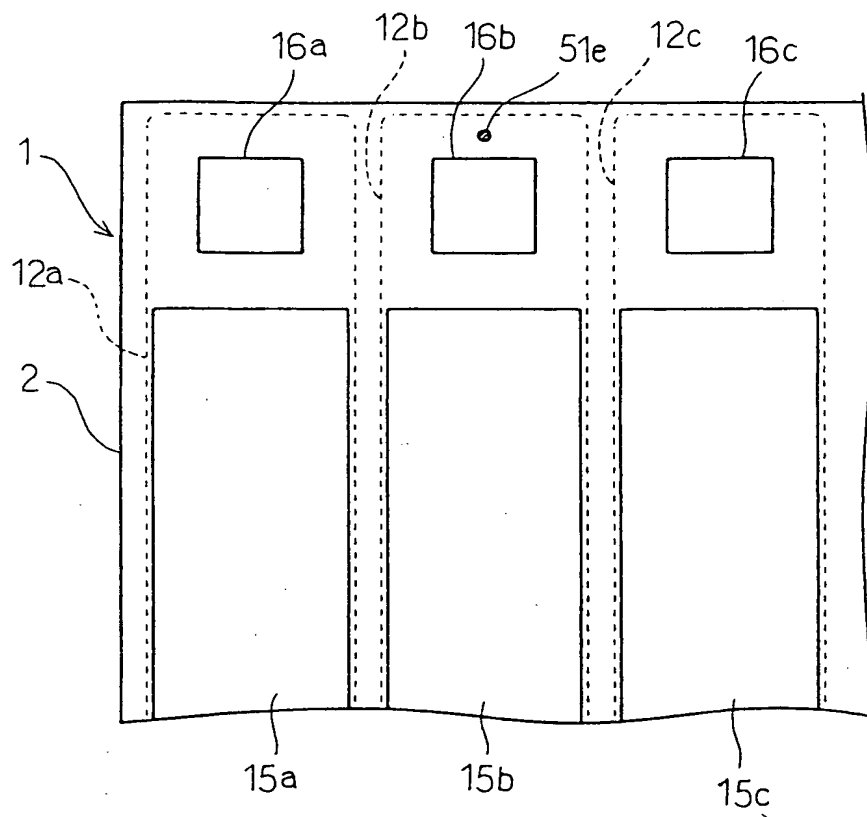


FIG. 14

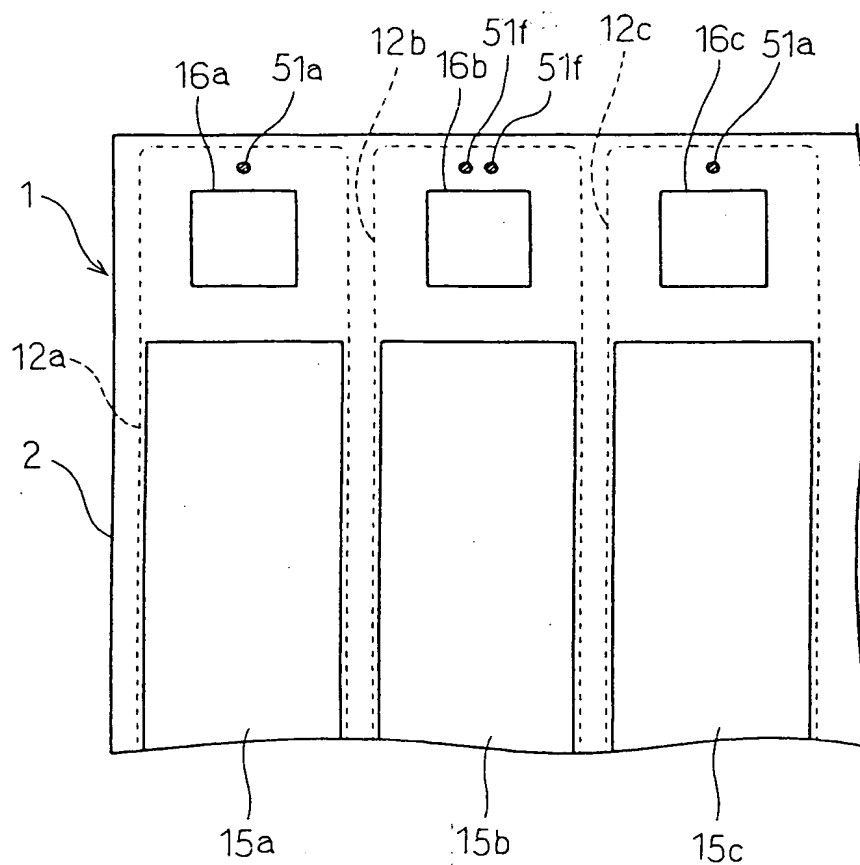


FIG. 15

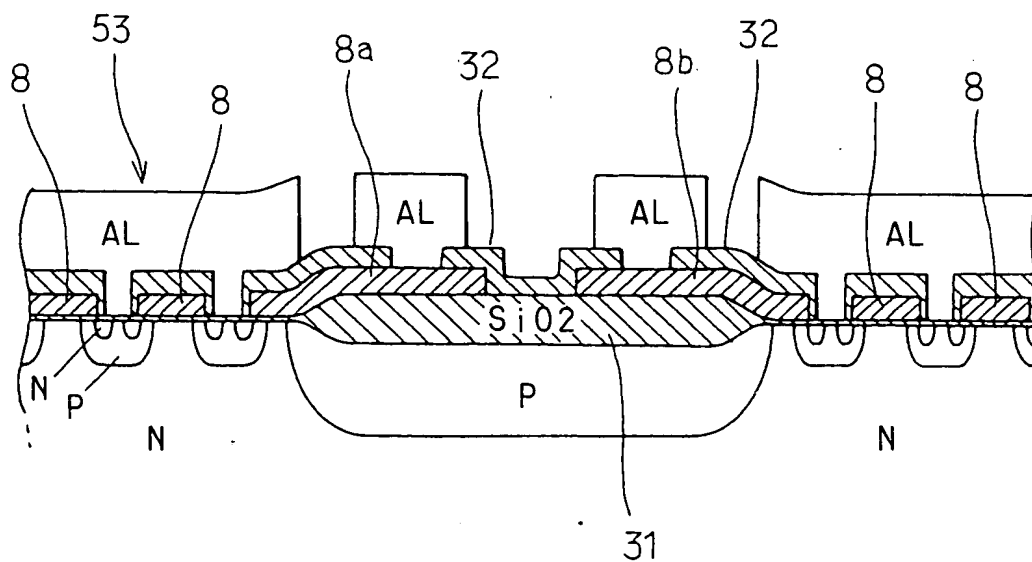


FIG. 16

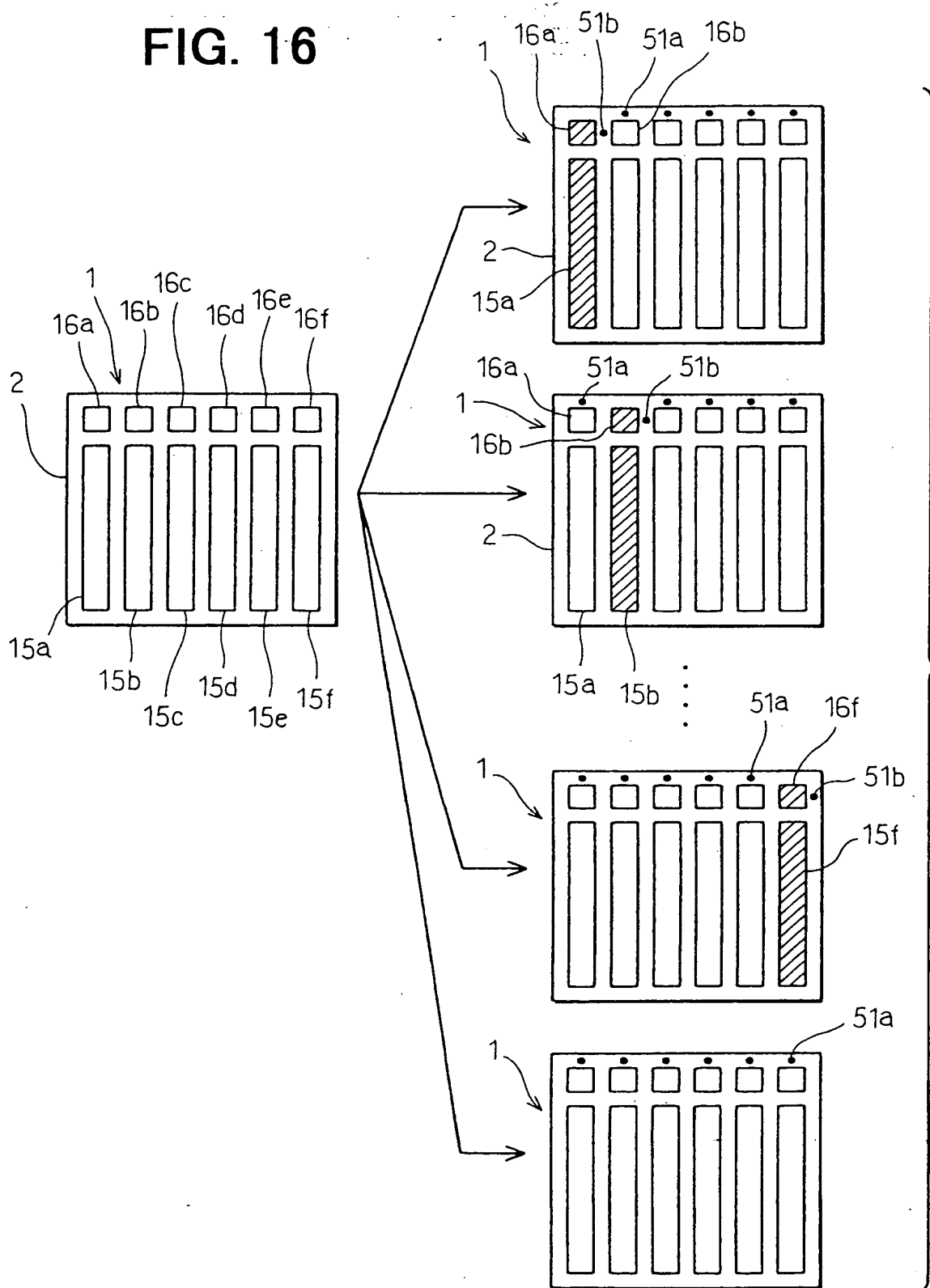


FIG. 17

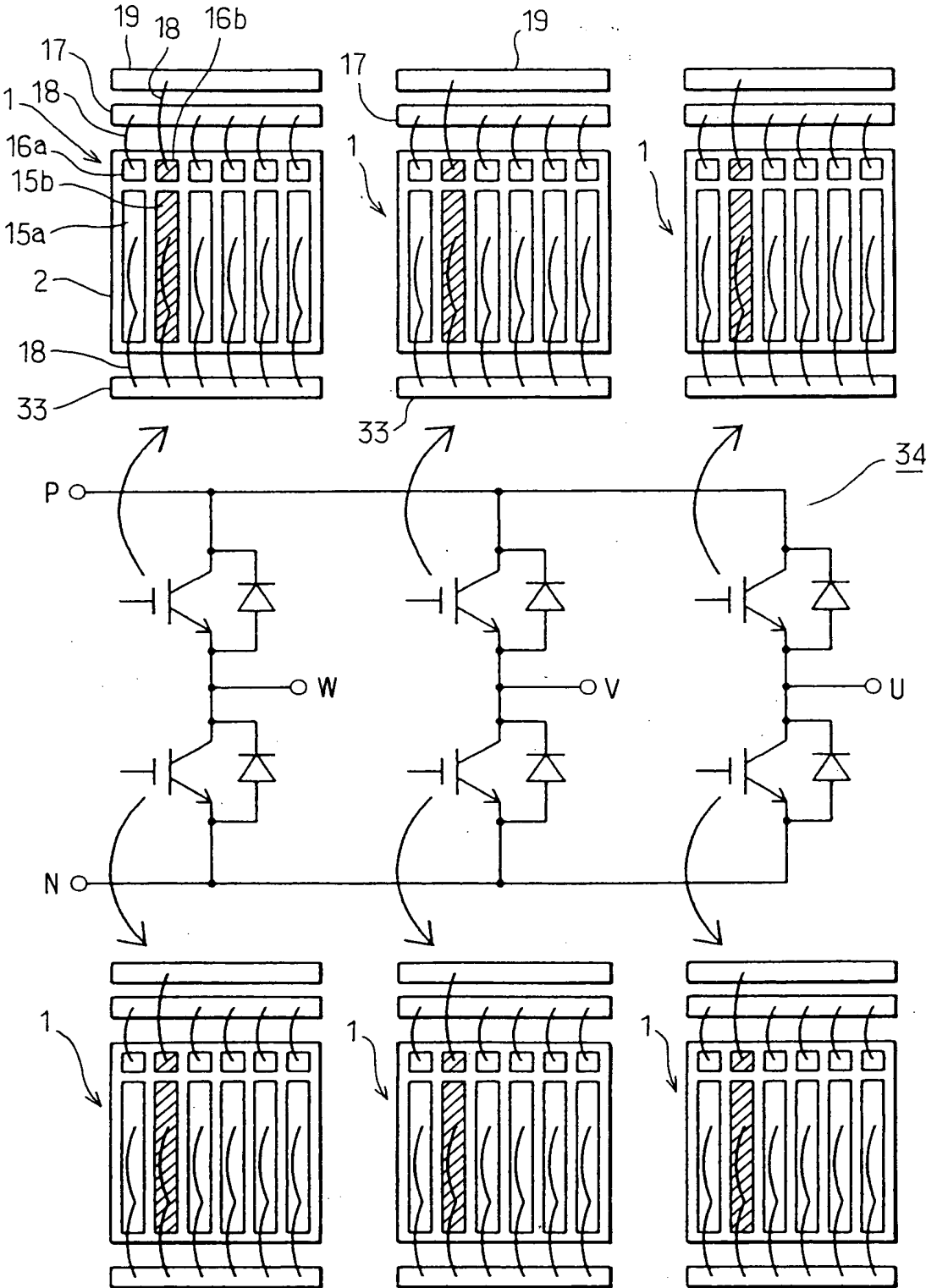


FIG. 18

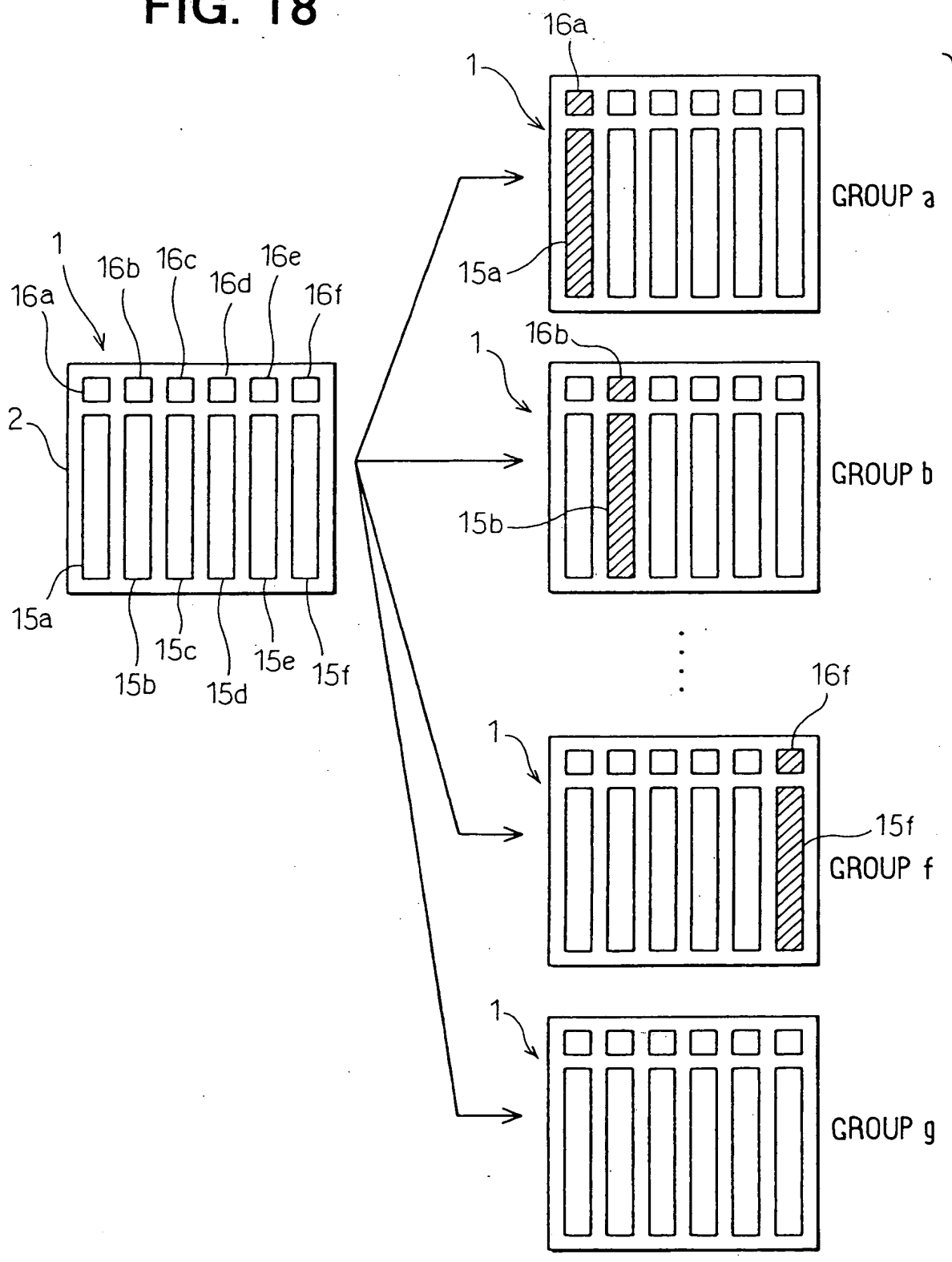


FIG. 19

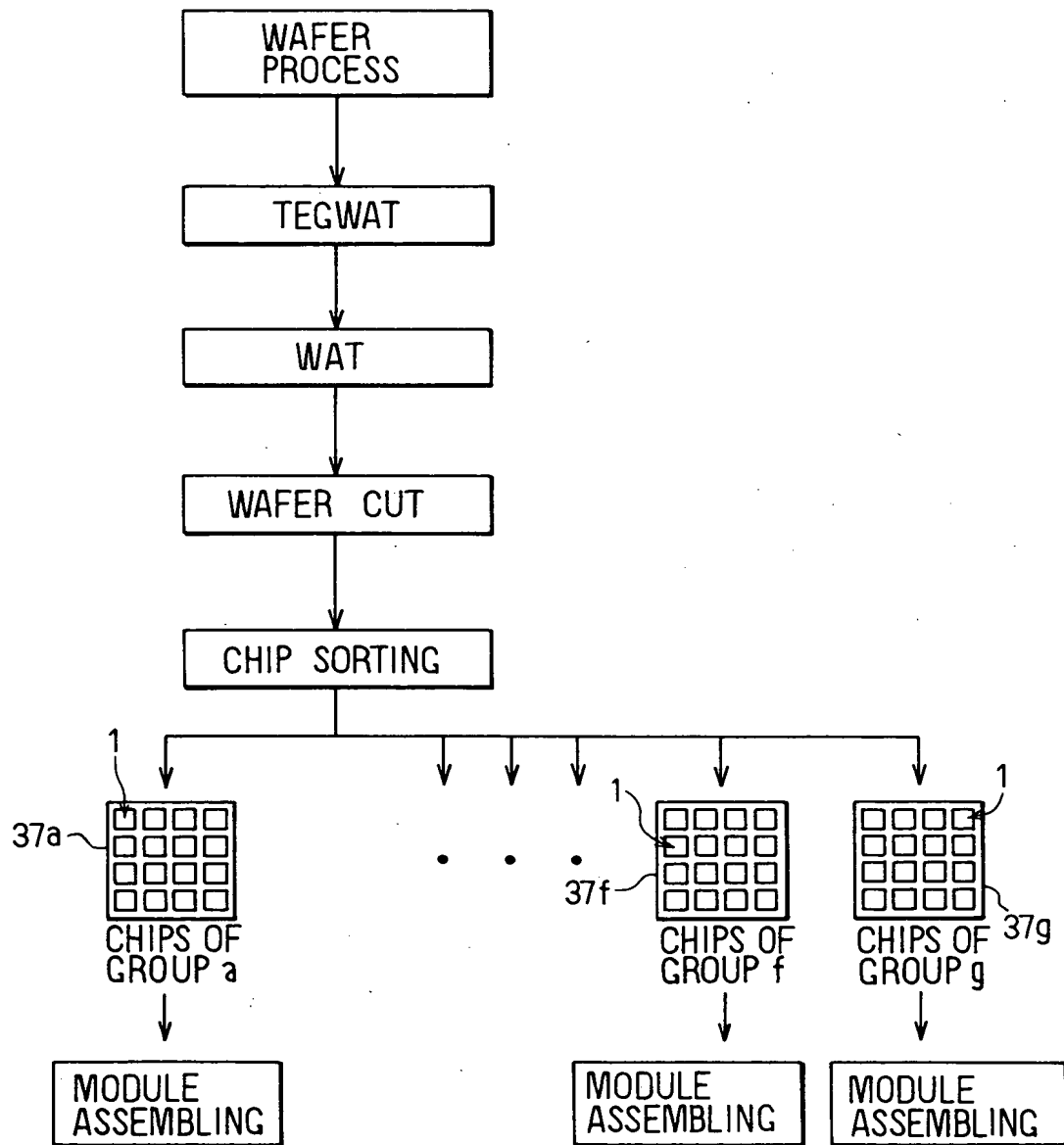


FIG. 20

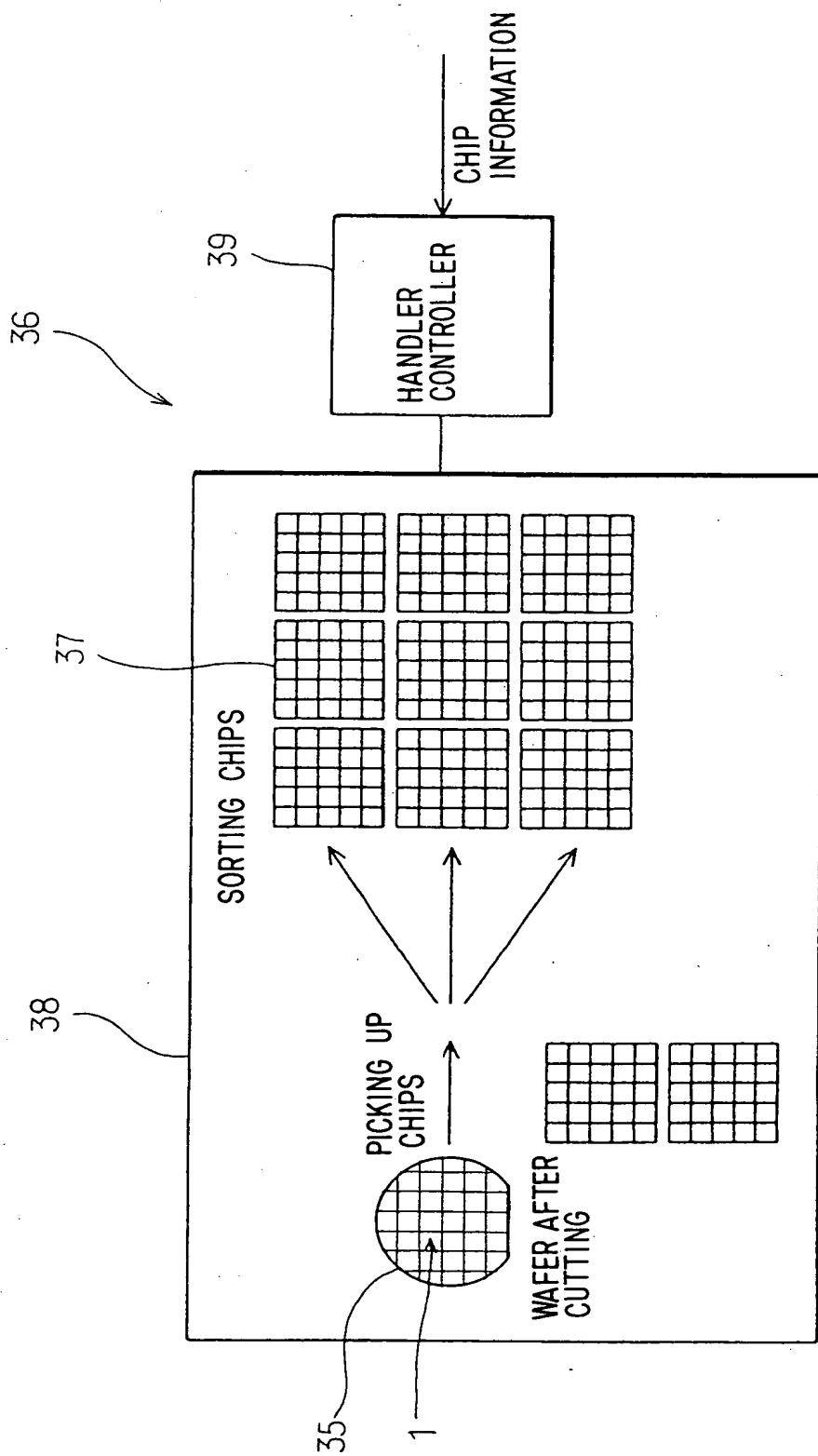


FIG. 21

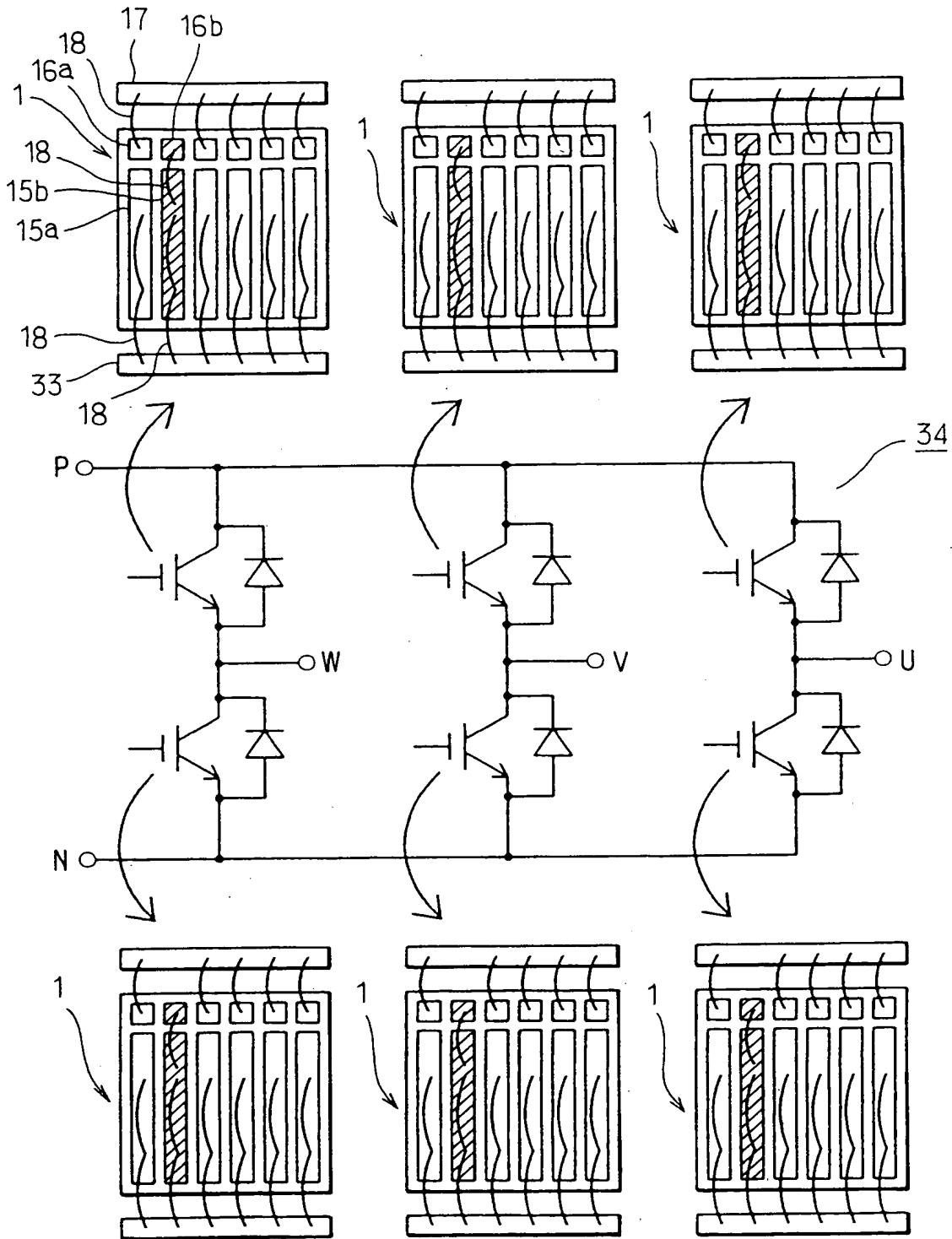


FIG. 22

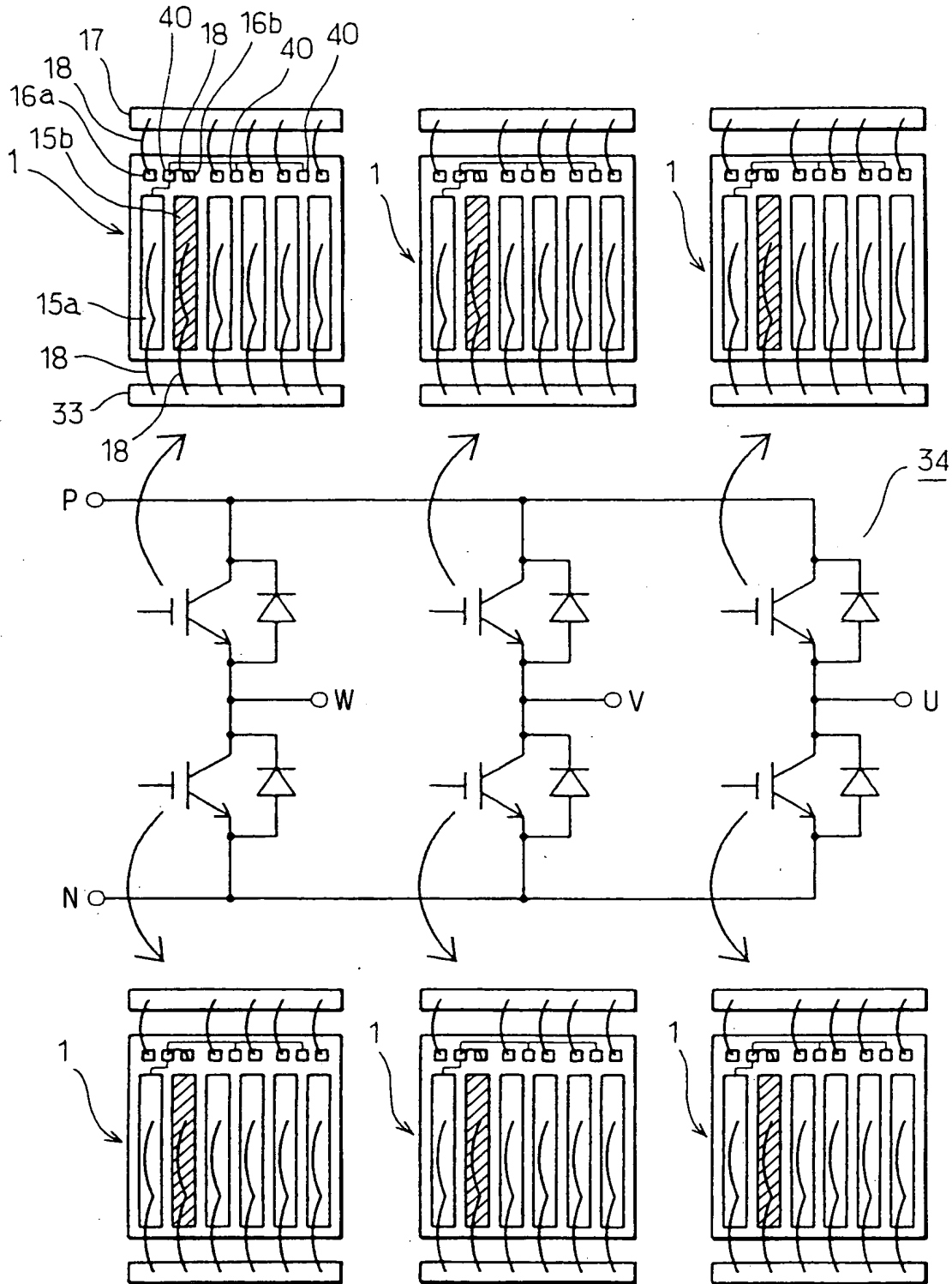


FIG. 23

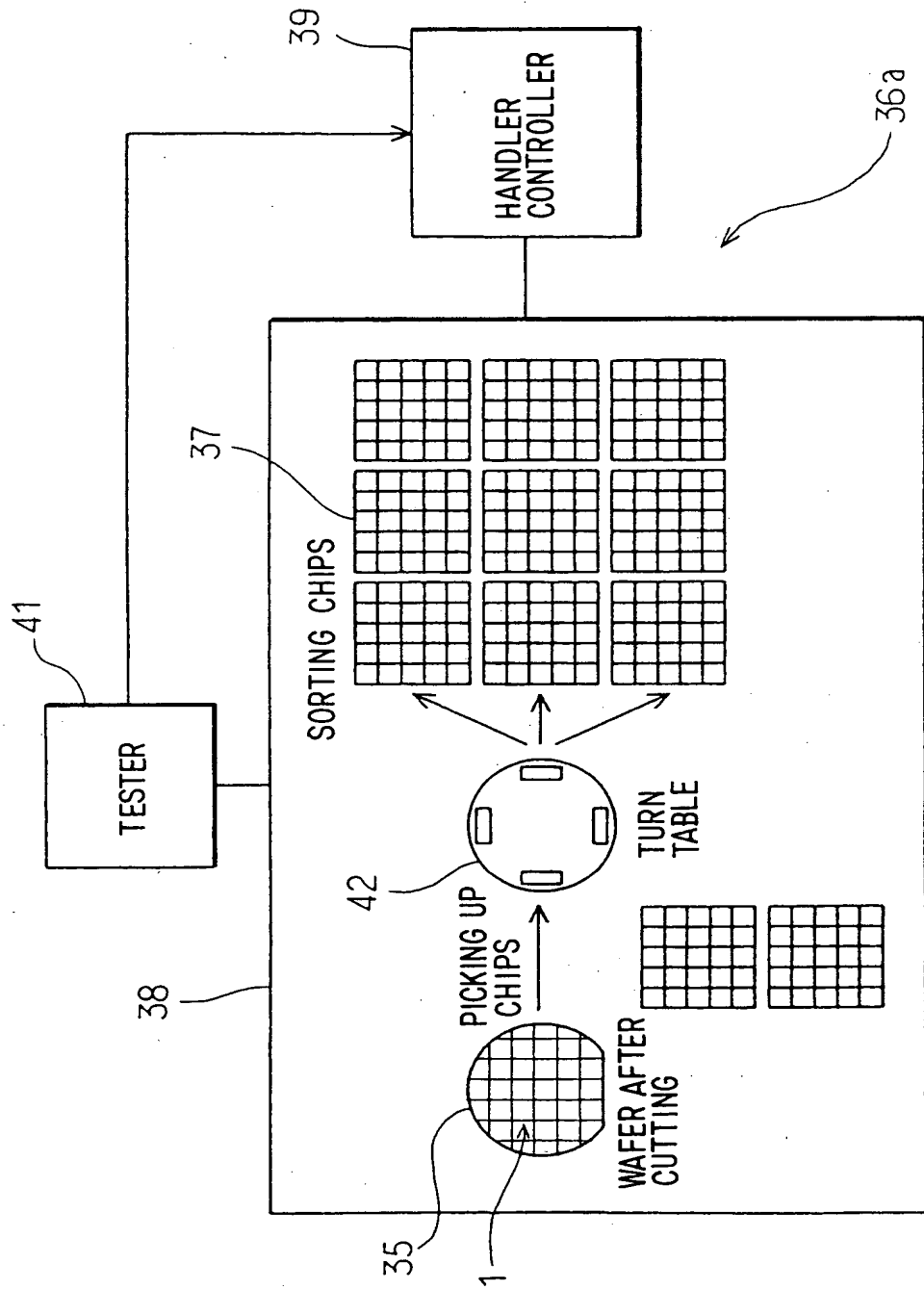


FIG. 24

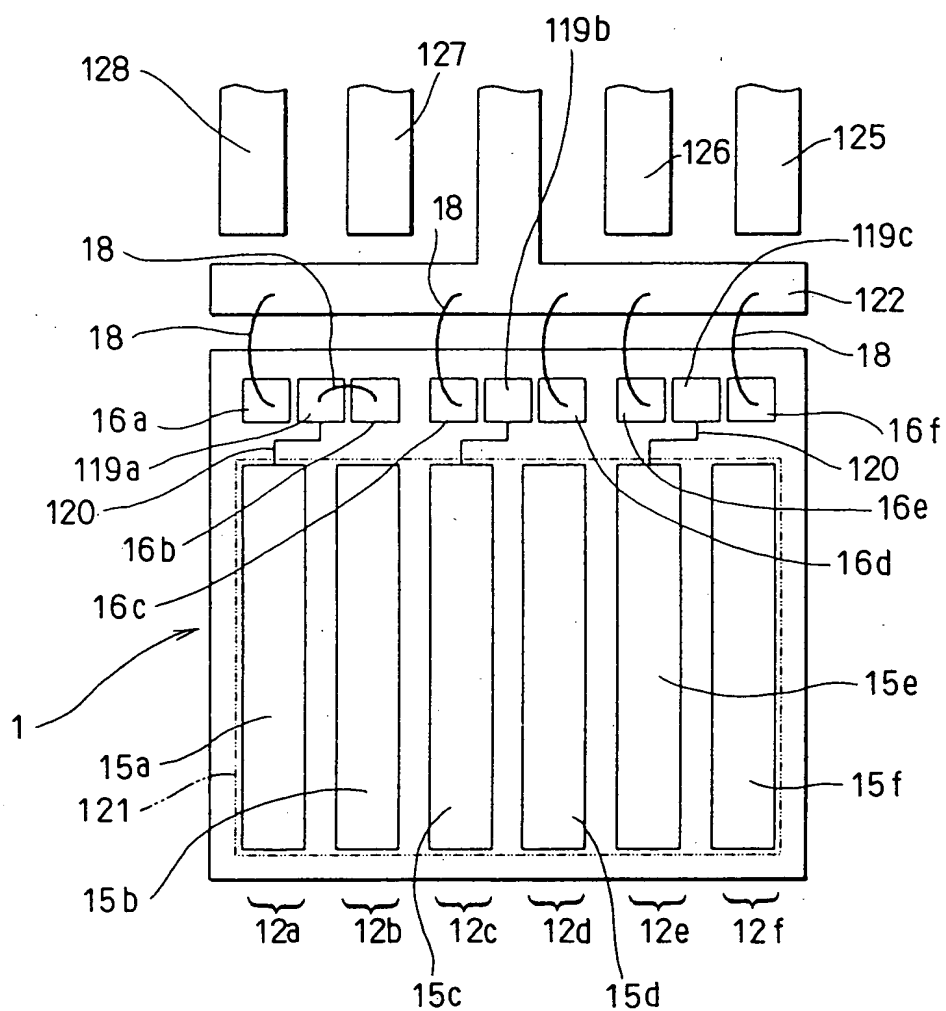


FIG. 25

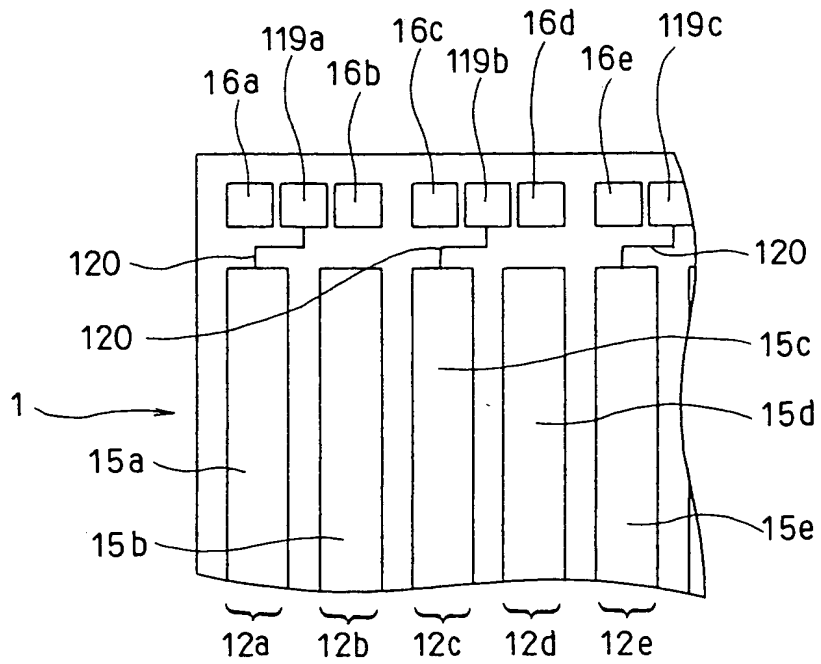


FIG. 27

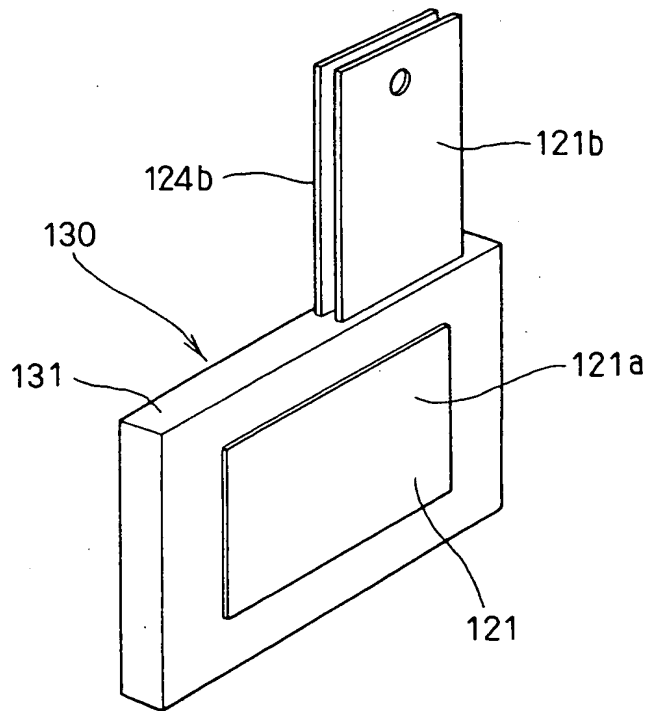


FIG. 26

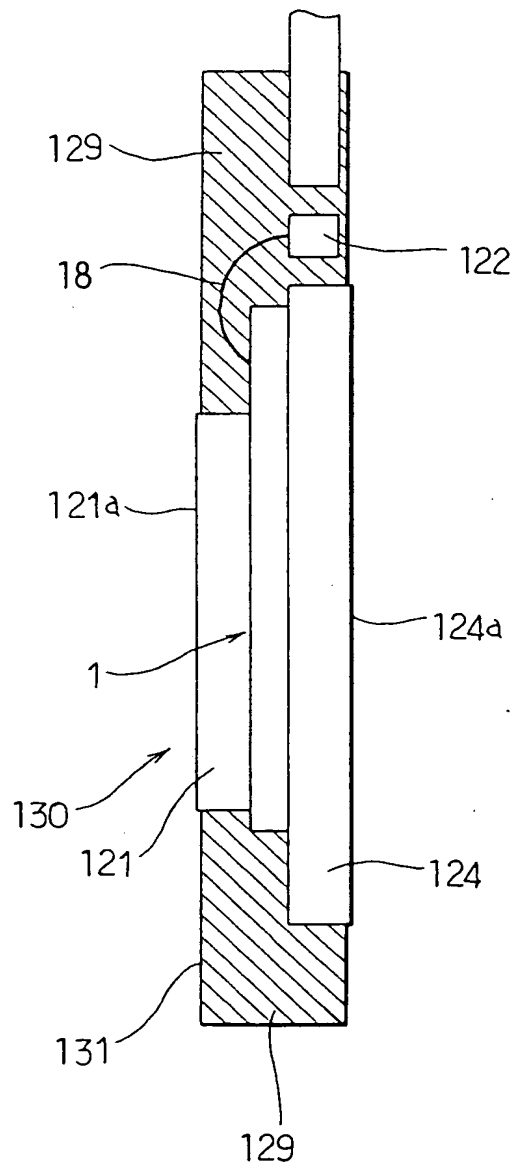


FIG. 28

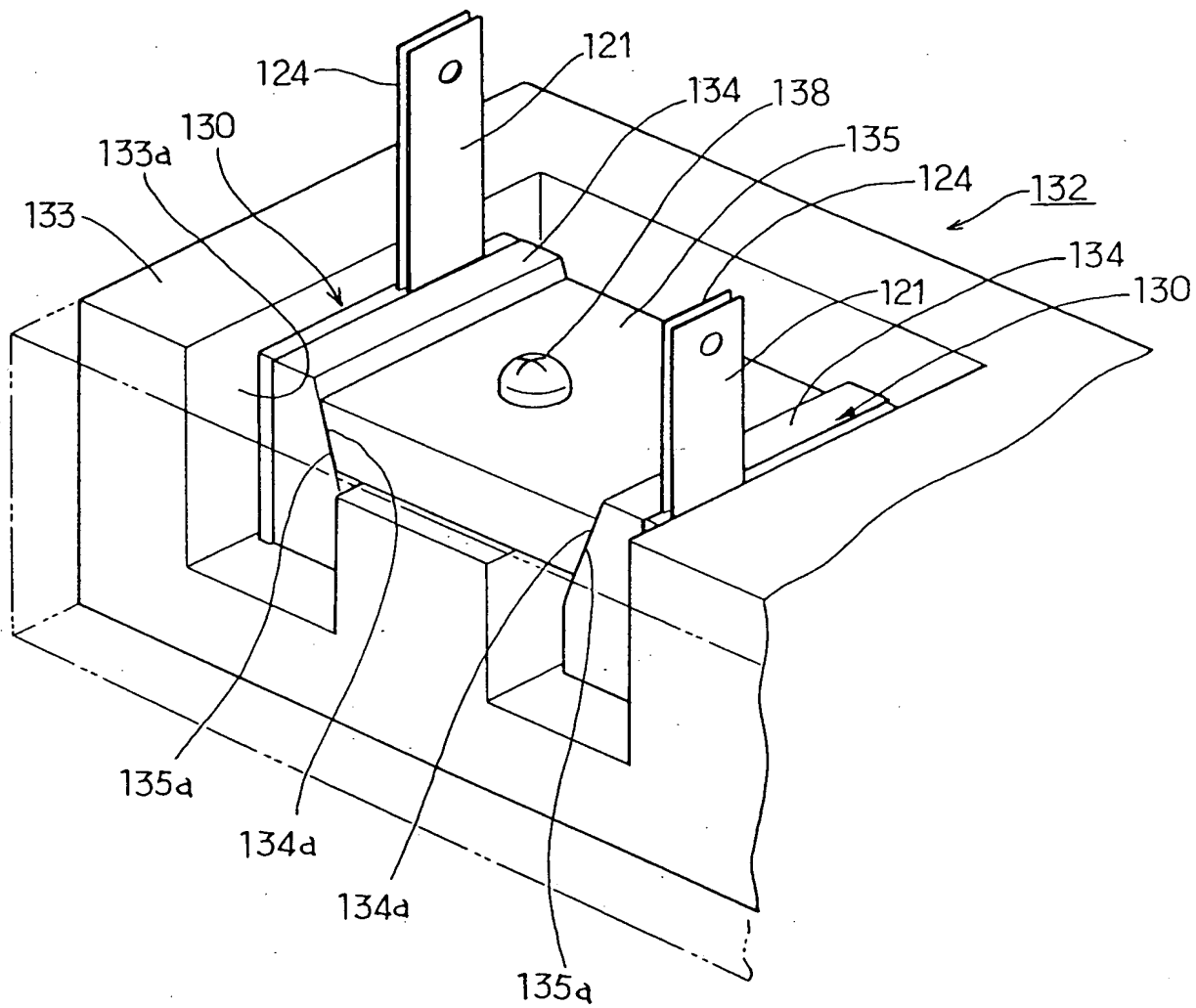


FIG. 30

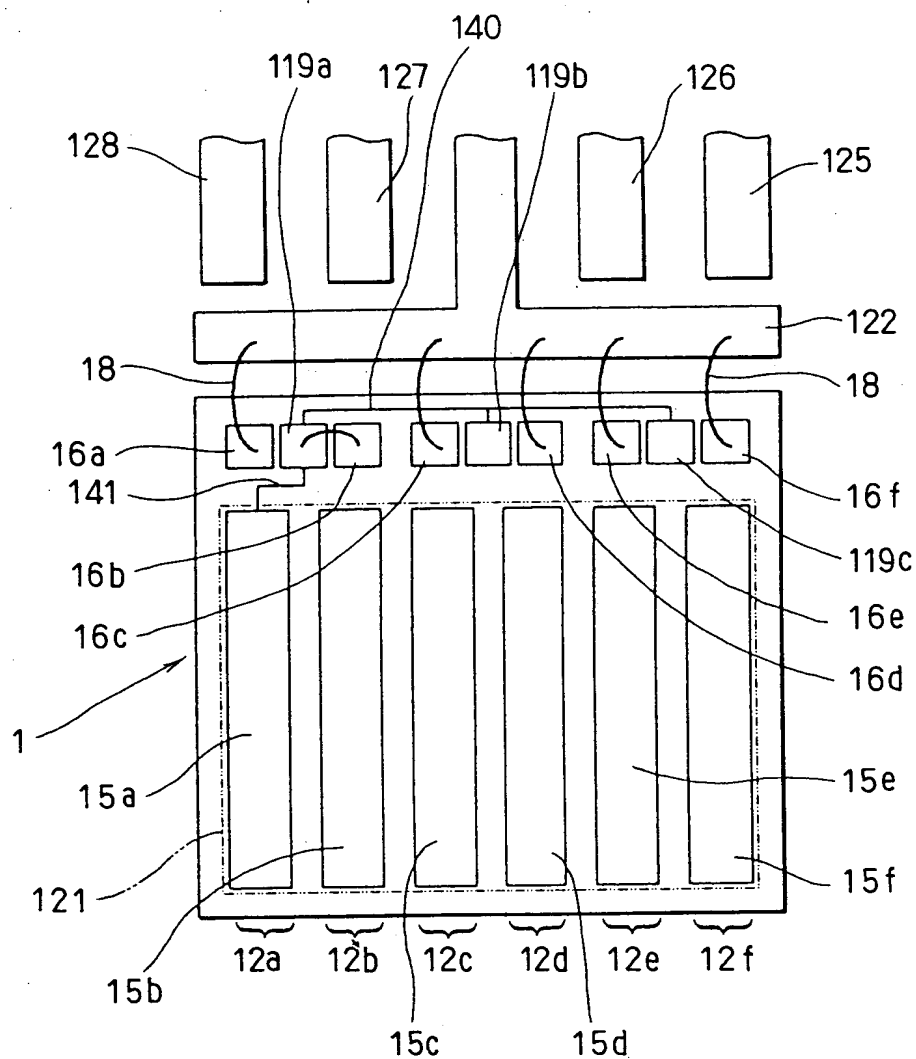


FIG. 31A

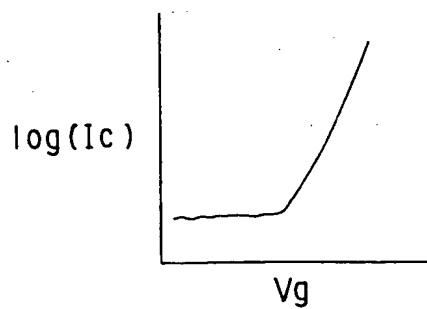


FIG. 31B

